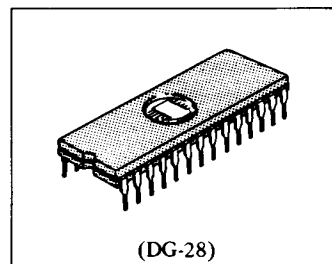


HN27256G Series

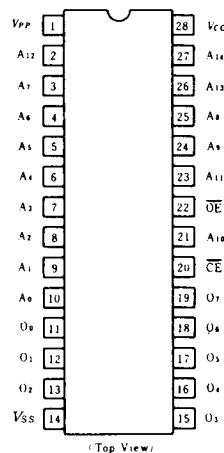
32768-word x 8-bit UV Erasable and Programmable ROM

■ FEATURES

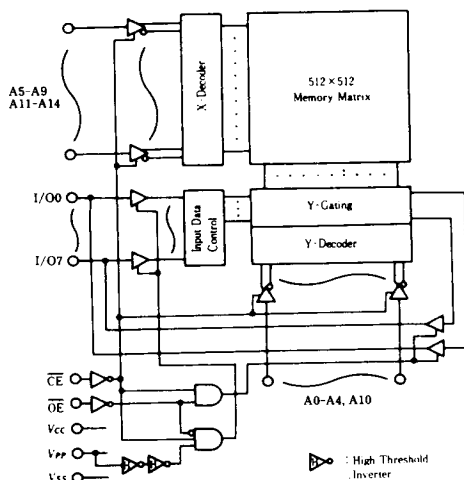
- Single Power Supply +5V $\pm$ 5%
- High Performance Programming . . Program Voltage: +12.5V D.C.
- Static No Clocks Required
- Inputs and Outputs TTL Compatible During Both Read and Program Modes
- Access Time HN27256G-25: 250ns(max.)
HN27256G-30: 300ns(max.)
- Absolute Max. Rating of V_{PP} pin . . 14.0V
- Low Stand-by Current 40mA max. (stand-by)
- Device Identifier Mode Manufacturer Code and Device Code



■ PIN ARRANGEMENT



■ BLOCK DIAGRAM



■ MODE SELECTION

Mode	Pins	$\overline{CE}$ (20)	$\overline{OE}$ (22)	A9 (24)	V_{PP} (1)	V_{CC} (28)	Outputs (11 - 13, 15 - 19)
Read		V_{IL}	V_{IL}	X	V_{CC}	V_{CC}	Dout
Output Disable		V_{IL}	V_{IH}	X	V_{CC}	V_{CC}	High Z
Standby		V_{IH}	X	X	V_{CC}	V_{CC}	High Z
High Performance Program		V_{IL}	V_{IH}	X	V_{PP}	V_{CC}	Din
Program Verify		V_{IH}	V_{IL}	X	V_{PP}	V_{CC}	Dout
Optional Verify		V_{IL}	V_{IL}	X	V_{PP}	V_{CC}	Dout
Program Inhibit		V_{IH}	V_{IH}	X	V_{PP}	V_{CC}	High Z
Identifier		V_{IL}	V_{IL}	V_H^{*2}	V_{CC}	V_{CC}	Code

Notes) *1. X: Don't care.
*2. V_H : 12.0V $\pm$ 0.5V.



Hitachi America Ltd. • 2210 O'Toole Ave. • San Jose, CA 95131 • (408) 435-8300

■ ABSOLUTE MAXIMUM RATING

Item	Symbol	Value	Unit
Operating Temperature Range	T_{opr}	0 to +70	°C
Storage Temperature Range	T_{stg}	- 65 to +125	°C
Storage Temperature Range Under Bias	T_{bias}	- 10 to +80	°C
All Input and Output Voltages*1	V_{IN}, V_{out}	-0.6 to +7	V
A9 Input Voltage*1	V_{ID}	-0.6 to +13.5	V
V_{PP} Voltage*1	V_{PP}	-0.6 to +14.0	V
V_{CC} Voltage*1	V_{CC}	-0.6 to +7	V

Note) *1. with respect to V_{SS} .

■ READ OPERATION

● DC AND OPERATING CHARACTERISTICS ($T_a = 0$ to +70°C, $V_{CC} = 5V \pm 5\%$, $V_{PP} = V_{CC}$)

Parameter	Symbol	Test Conditions	min.	typ.	max.	Unit
Input Leakage Current	I_{LI}	$V_{IN} = 5.25V$	-	-	10	μA
Output Leakage Current	I_{LO}	$V_{out} = 5.25V/0.45V$	-	-	10	μA
V_{PP} Current	I_{PP1}	$V_{PP} = 5.5 V$	-	-	5	mA
V_{CC} Current (Standby)	I_{CC1}	$\overline{CE} = V_{IH}$	-	-	40	mA
V_{CC} Current (Active)	I_{CC2}	$\overline{CE} = \overline{OE} = V_{IL}$	-	45	100	mA
Input Low Voltage	V_{IL}		-0.1*1	-	0.8	V
Input High Voltage	V_{IH}		2.0	-	$V_{CC} + 1$ *2	V
Output Low Voltage	V_{OL}	$I_{OL} = 2.1 mA$	-	-	0.45	V
Output High Voltage	V_{OH}	$I_{OH} = -400 \mu A$	2.4	-	-	V

*: V_{IL} min. = -0.6V for pulse width $\leq 20ns$.

** : V_{IH} max. = $V_{CC} + 1.5V$ for pulse width $\leq 20ns$. If V_{IH} is over the specified maximum value, read operation cannot be guaranteed.

● AC CHARACTERISTICS ($T_a = 0 \sim 70^\circ C$, $V_{CC} = 5V \pm 5\%$, $V_{PP} = V_{CC}$)

Parameter	Symbol	Test Condition	HN27256G-25		HN27256G-30		Unit
			min.	max.	min.	max.	
Address to Output Delay	t_{ACC}	$\overline{CE} = \overline{OE} = V_{IL}$	-	250	-	300	ns
$\overline{CE}$ to Output Delay	t_{CE}	$\overline{OE} = V_{IL}$	-	250	-	300	ns
$\overline{OE}$ to Output Delay	t_{OE}	$\overline{CE} = V_{IL}$	-	100	-	120	ns
$\overline{OE}$ High to Output Float	t_{DF}	$\overline{CE} = V_{IL}$	0	60	0	105	ns
Address to Output Hold	t_{OH}	$\overline{CE} = \overline{OE} = V_{IL}$	0	-	0	-	ns

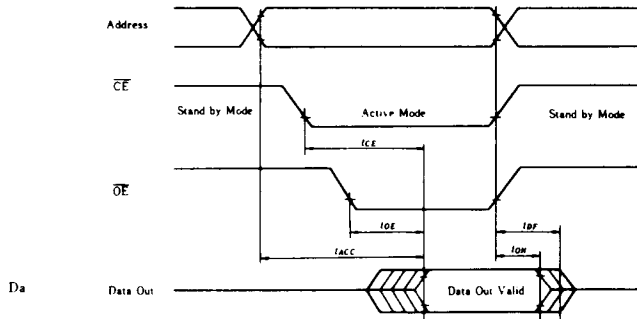
Note: t_{DF} defines the time at which the Output achieves the open circuit condition and Data is no longer driven.

● SWITCHING CHARACTERISTICS

TEST CONDITION

Input pulse levels: 0.45V to 2.4V
 Input rise and fall time: $\leq 20ns$
 Output load: 1 TTL Gate +100pF
 Reference level for measuring timing: 0.8V and 2V



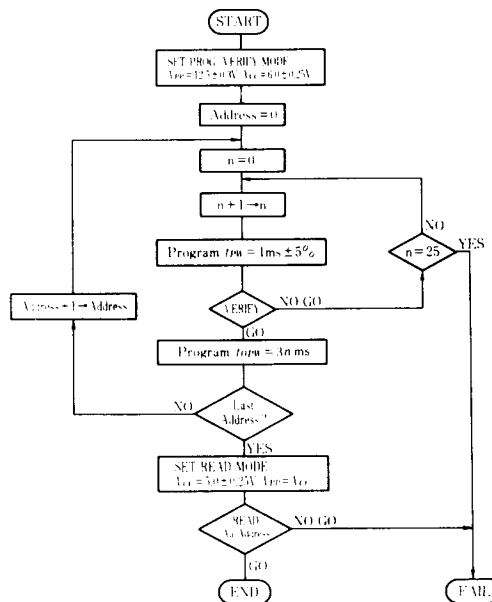


■ CAPACITANCE ($T_a=25^\circ\text{C}$, $f=1\text{MHz}$)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit.
Input Capacitance	C_{in}	$V_{in} = 0\text{ V}$	—	4	6	pF
Output Capacitance	C_{out}	$V_{out} = 0\text{ V}$	—	8	12	pF

■ HIGH PERFORMANCE PROGRAMMING

This device can be applied the High Performance Programming algorithm shown in following flowchart. This algorithm allows to obtain faster programming time without any voltage stress to the device nor deterioration in reliability of programmed data.



High Performance Programming Flowchart



■ HIGH PERFORMANCE PROGRAMMING OPERATION

- DC PROGRAMMING CHARACTERISTICS ($T_a=25^{\circ}\text{C}\pm 5^{\circ}\text{C}$, $V_{CC}=6\text{V}\pm 0.25\text{V}$, $V_{PP}=12.5\text{V}\pm 0.3\text{V}$)

Parameter	Symbol	Test Condition	min.	typ.	max.	Unit
Input Leakage Current	I_{LI}	$V_{IN} = 5.25\text{ V}$	—	—	10	μA
Output Low Voltage During Verify	V_{OL}	$I_{OL} = 2.1\text{ mA}$	—	—	0.45	V
Output High Voltage During Verify	V_{OH}	$I_{OH} = -400\text{ }\mu\text{A}$	2.4	—	—	V
V_{CC} Current (Active)	I_{CC2}		—	—	100	mA
Input Low Level	V_{IL}		-0.1*1	—	0.8	V
Input High Level	V_{IH}		2.0	—	$V_{CC}+0.5$ *2	V
V_{PP} Supply Current	I_{PP2}	$\overline{\text{CE}} = V_{IL}$	—	—	50	mA

Notes) *1. -0.6V for pulse width $\leq 20\text{ns}$.

*2. If V_{IH} is over the specified maximum value, programming operation cannot be guaranteed.

- AC PROGRAMMING CHARACTERISTICS ($T_a=25^{\circ}\text{C}\pm 5^{\circ}\text{C}$, $V_{CC}=6\text{V}\pm 0.25\text{V}$, $V_{PP}=12.5\text{V}\pm 0.3\text{V}$)

Parameter	Symbol	Test Condition	min.	typ.	max.	Unit
Address Setup Time	t_{AS}		2	—	—	μs
$\overline{\text{OE}}$ Setup Time	t_{OES}		2	—	—	μs
Data Setup Time	t_{DS}		2	—	—	μs
Address Hold Time	t_{AH}		0	—	—	μs
Data Hold Time	t_{DH}		2	—	—	μs
$\overline{\text{OE}}$ to Output Float Delay	t_{DF}^{*1}		0	—	130	ns
V_{PP} Setup Time	t_{VPS}		2	—	—	μs
V_{CC} Setup Time	t_{VCS}		2	—	—	μs
$\overline{\text{OE}}$ Pulse Width During Initial Programming	t_{PW}		0.95	1.0	1.05	ms
$\overline{\text{CE}}$ Pulse Width During Overprogramming	t_{OPW}^{*1}		2.85	—	78.75	ms
Data Valid from $\overline{\text{OE}}$	t_{OE}		—	—	150	ns

Note) *1. t_{OPW} is defined as mentioned in flow chart. t_{DF} defines the time at which the output achieves the open circuit condition and data is no longer driven.

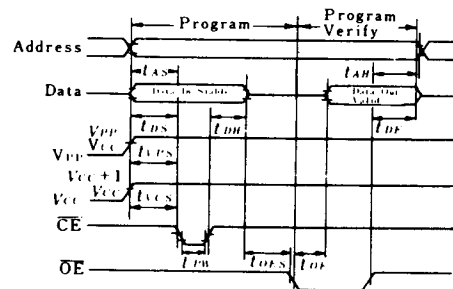
● SWITCHING CHARACTERISTICS

Test Condition

Input pulse level: 0.45 to 2.4V

Input rise and fall time: $\leq 20\text{ns}$

Reference level for measuring time: 0.8V and 2V



■ ERASE

Erasure of HN27256G is performed by exposure to ultraviolet light of 2537Å and all the output data are changed to "1" after this erasure procedure. The minimum integrated dose (i.e. UV intensity x exposure time) for erasure is 15W. sec/cm².



■ DEVICE IDENTIFIER MODE

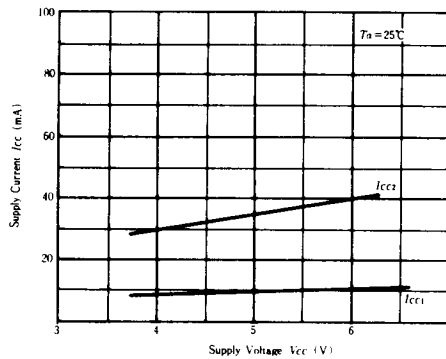
The Identifier Mode allows the reading out of binary codes that identify Manufacturer and type of device, from outputs of EPROM. By this Mode, the device will be automatically matched its own corresponding programming algorithm, using programming equipment.

● HN27256G SERIES IDENTIFIER CODE

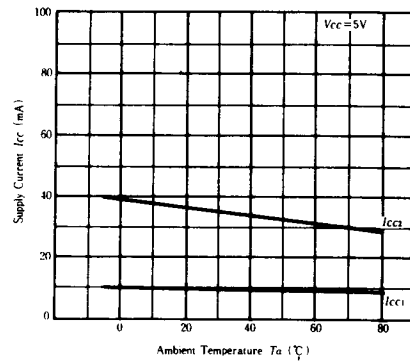
Pins	A ₀ (10)	O ₇ (19)	O ₆ (18)	O ₅ (17)	O ₄ (16)	O ₃ (15)	O ₂ (13)	O ₁ (12)	O ₀ (11)	Hex Data
Identifier										
Manufacturer Code	V _{IL}	0	0	0	0	0	1	1	1	07
Device Code	V _{IH}	0	0	0	1	0	0	0	0	10

Notes: 1. A₉ = 12.0V ± 0.5V.
2. A₁ - A₈, A₁₀ - A₁₄, $\overline{CE}$, $\overline{OE}$ = V_{IL}.

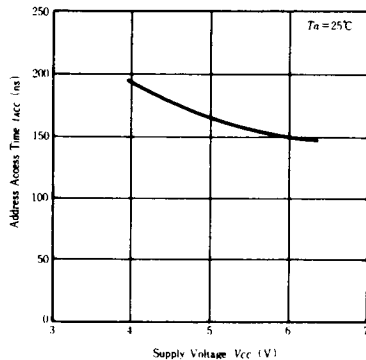
SUPPLY CURRENT VS. SUPPLY VOLTAGE



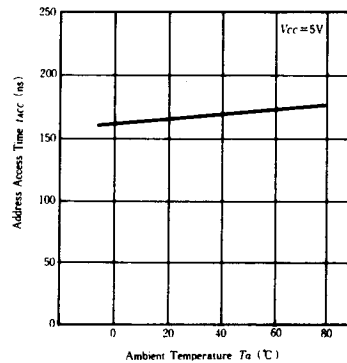
SUPPLY CURRENT VS. AMBIENT TEMPERATURE



ADDRESS ACCESS TIME VS. SUPPLY VOLTAGE



ADDRESS ACCESS TIME VS. AMBIENT TEMPERATURE



Hitachi America Ltd. • 2210 O'Toole Ave. • San Jose, CA 95131 • (408) 435-8300